



P-Channel Enhancement Mode Field Effect Transistor

Product Summary

| | |
|-----------------------------------|-------|
| V_{DS} | -100V |
| I_D | -26A |
| $R_{DS(ON)}$ (at $V_{GS}=-10V$) | 52m |
| 100% EAS Tested | |



Typical Electrical and Thermal Characteristics Diagrams

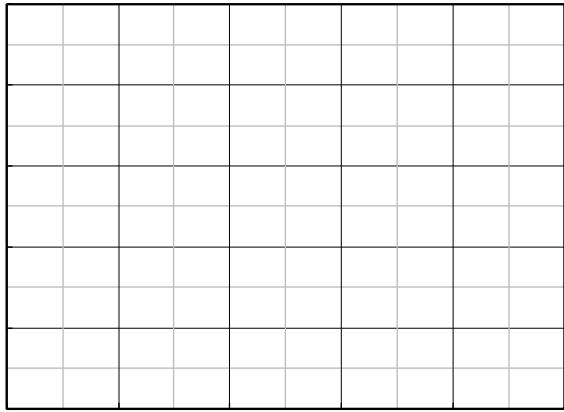


Figure 1. Output Characteristics; typical values

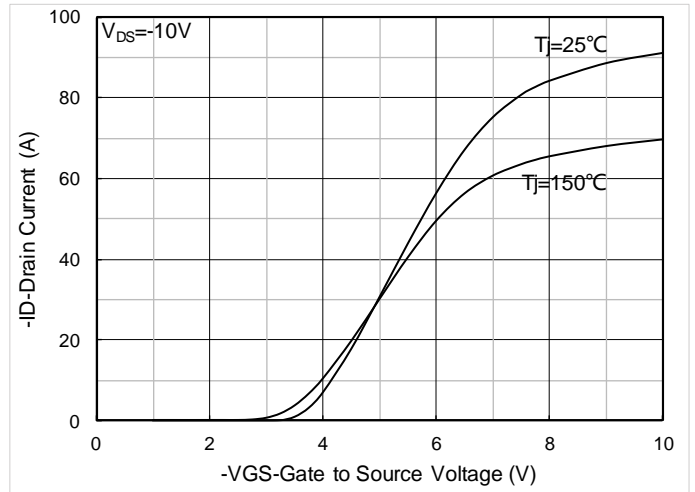


Figure 2. Transfer Characteristics; typical values

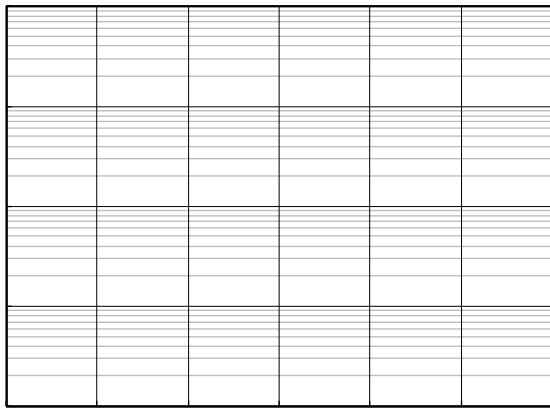


Figure 3. Capacitance Characteristics; typical values

Figure 4. Gate Charge; typical values

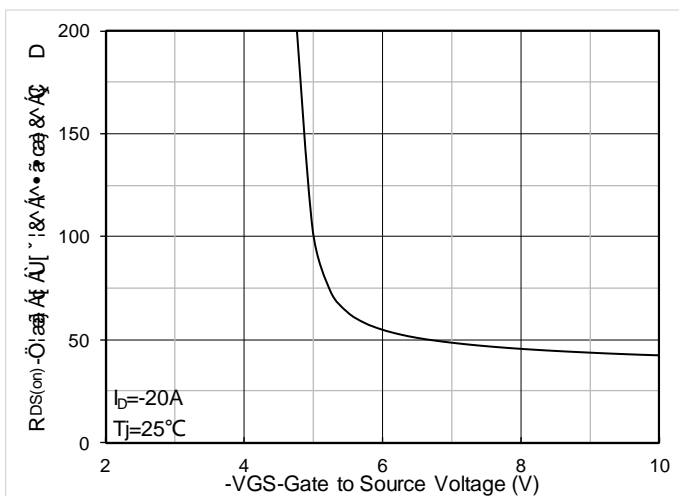


Figure 5. On-Resistance vs Gate to Source Voltage; typical values

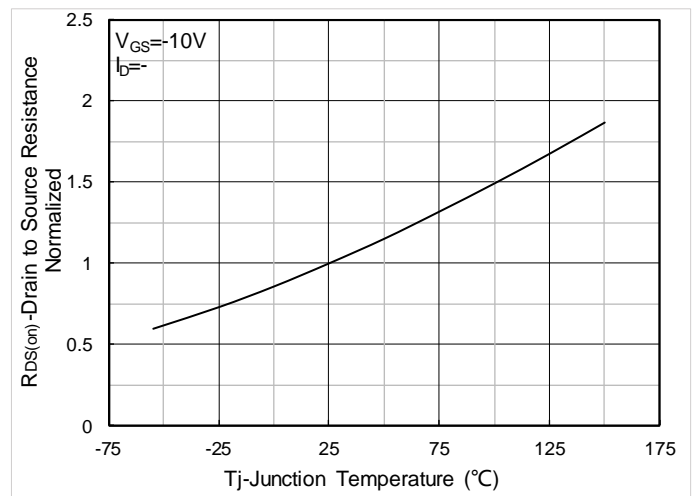
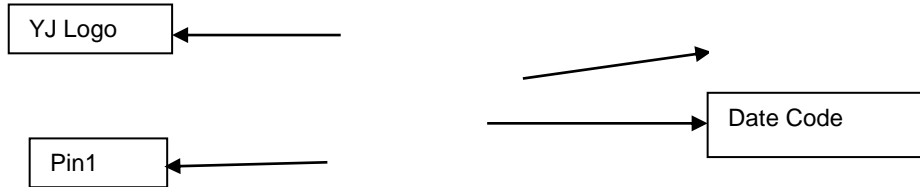


Figure 6. Normalized On-Resistance

YJG052GP10H



Marking Information



Note

1. All marking is at middle of the product body
2. All marking is in laser printing
3. YJG052GP10H is Marking Code, YYWW is date code, %Y^% A^% E% Y ^% A ^%\
4. Body color: Black

